



MMA-172135-M5 17-21GHz, 3W Power Amplifier

Features:

• Frequency Range: 17 – 21 GHz

• P1dB: 35 dBm

IM3 Level -45dBc @Po=20dBm/tone

Gain: 27 dBVdd =6 V

• Ids = 1500 to 2800 mA

Input and Output Fully Matched to 50 Ω

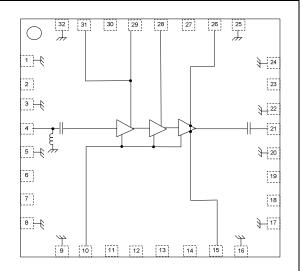
Surface Mount, RoHs Compliant QFN 5x5mm package

Applications:

Communication systems

Microwave instrumentations

• Point to Point Radios



Functional Block Diagram

Description:

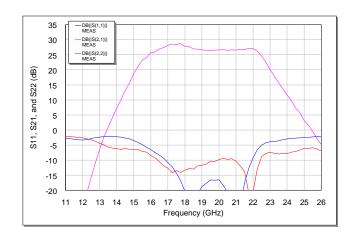
The MMA-172135-M5 is a broadband GaAs MMIC Power amplifier with 3-Watt output power and high gain of 27dB over full 17 to 21GHz frequency range. This amplifier was optimally designed for high linearity applications at 12dB back-off from P-1 condition.

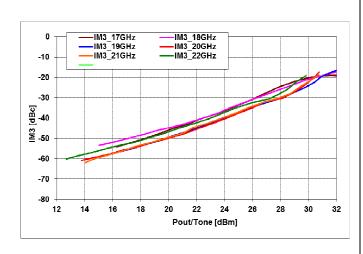
Absolute Maximum Ratings: (Ta= 25 ℃)*

SYMBOL	PARAMETERS	UNITS	Min.	Max.		
Vds	Drain-Source Voltage	V		6.5		
Vg	Gate-Source Voltage	V	-2.1	0		
lg	First Gate Current	mA	-17	17		
Pd	Power Dissipation	W		16.8		
Pin max	RF Input Power	dBm		20		
Toper	Operating Temperature	°C		-40 to +85		
Tch	Channel Temperature	°C		+150		
Tstg	Storage Temperature	°C		-55 to +150		
Tmax	Max. Assembly Temp (20 sec max)	°C		+250		
*Operation of this device above any one of these parameters may cause permanent damage.						

Electrical Specifications: vds=6v, vg=-0.85v, lds=2000mA, Ta=25 ℃ Z0=50 ohm					
Parameter	Units	Typical Data			
Frequency Range	GHz	17 - 21			
Gain (Typ / Min)	dB	27 / 26			
Gain Flatness (Typ / Max)	+/-dB	1 / 1.5			
Input RL(Typ/Max)	dB	12/10			
Output RL(Typ/Max)	dB	12/10			
Output P1dB(Typ/Min)	dBm	34.5/33.5			
IM3 Level @Po=20dBm/tone	dBc	-45			
Output Psat(Typ/Min)	dBm	36/35.5			
Operating Current at P1dB (Typ/Max)	mA	2000 / 2500			
Thermal Resistance	°C /W	3.8			
(1) Output IM3 is measured with two tones at output power of 20 dBm/tone separated by 20 MHz.					

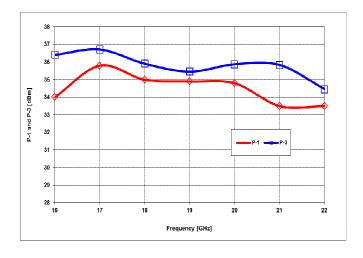
Typical RF Performance: Vds=6V, Vg=-0.85V, Ids=2000mA, Z0=50 ohm, Ta=25 °C

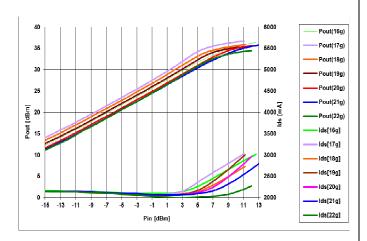




S11[dB], S21[dB], and S22[dB] vs. Frequency

IM3 Level [dBc] vs. output power/tone [dBm]

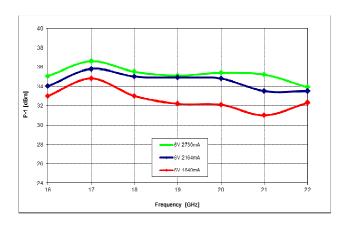




P-1 and Psat vs. Frequency

Pout[dBm], and Ids[mA] vs. Input power [dBm]

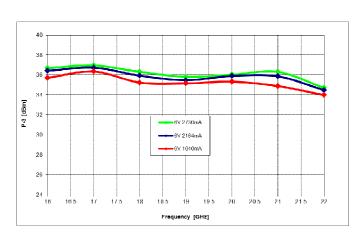
Typical Bias dependent RF Performance:

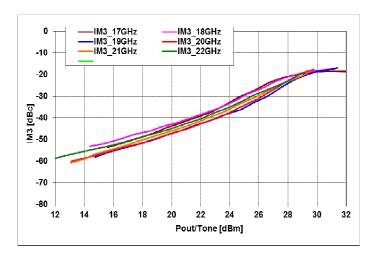


-IM3_18GHz -IM3_20GHz -IM3_22GHz 0 -IM3_17GHz -IM3_19GHz -IM3_21GHz -10 -20 -30 일 -40 ≌ -50 -60 -70 -80 12 22 24 28 30 32 14 16 18 26 Pout/Tone [dBm]

Bias dependent P1 vs. Frequency

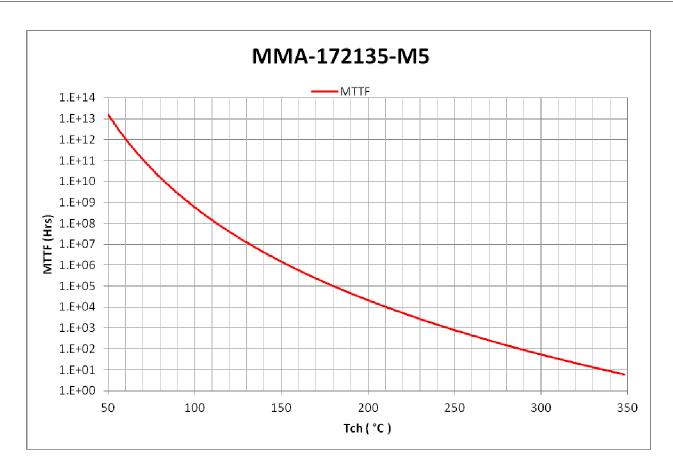
IM3 Level [dBc] vs. output power/tone [dBm] @Vds=6V, Idsq=2.5A





Bias dependent P-3 vs. Frequency

Pout[dBm], and Ids[mA] vs. Input power [dBm] @Vds=6V, Idsq=1.5A



This plot is based on MTTF data provided by wafer foundry and is scaled to the size of this MMIC size.



Applications

The MMA-172135-M5 MMIC power amplifier is designed for use as a power stage amplifier in microwave transmitters. It is ideally suited for 17 to 21GHz band point to point radio applications requiring a flat gain response and excellent linearity performance. This amplifier is provided as a 5x5mm QFN package, and the packaged amplifier is fully compatible with industry standard high volume surface mount PCB assembly processes.

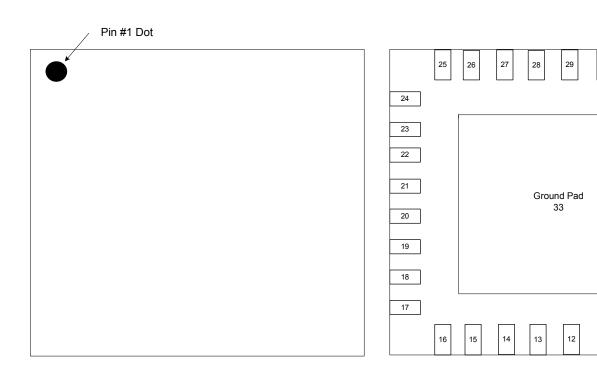
Biasing and Operation

The recommended bias conditions for best performance for the MMA-172135-M5 are VDD = 6.0V, Idsq = 2000mA. Performance improvements are possible depending on applications. The drain bias voltage range is 5 to 6V and the quiescent drain current biasing range is 1500mA to 2800mA. A single DC gate supply connected to Vg will bias all the amplifier stages. Muting can be accomplished by setting Vg to the pinch-off voltage (Vp=-2V). The gate voltage (Vg) should be applied prior to the drain voltages (Vd1, Vd2, Vd3) during power up and removed after the drain voltages during power down. The RF input and output ports are DC decoupled internally. Typical DC supply connection with bi-passing capacitors for the MMA-172135-M5 is shown in following pages.

Assembly Techniques

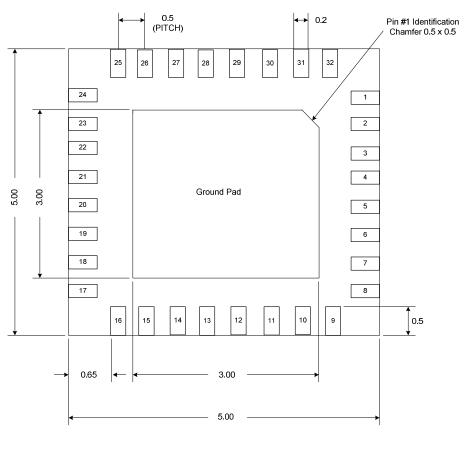
GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly. MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.

Package Pin-out:



Pin	Description
4	RF Input
21	RF Output
10	Vg
31	Vd1
28	Vd2
15, 26	Vd3
1, 3, 5, 8 ,9, 16, 17, 20, 22,	Ground
24, 25, 32, 33	
2, 6, 7, 11, 12, 13, 14, 18,	N/C
19, 23, 27, 29, 30	

Mechanical Information:



BOTTOM VIEW

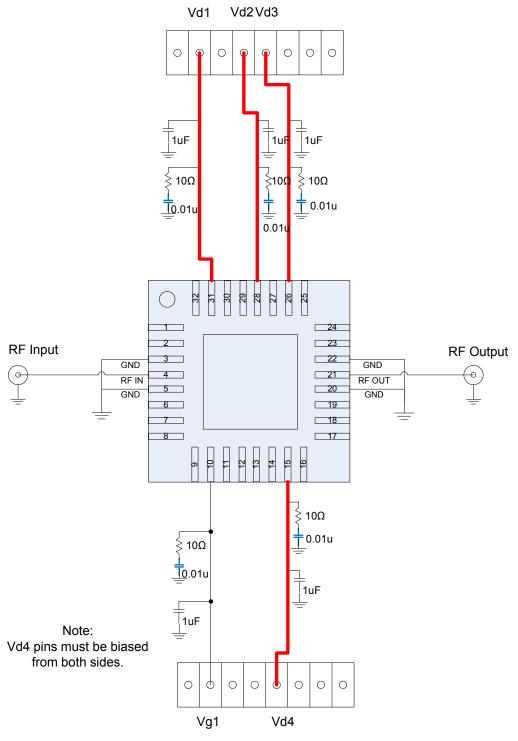


SIDE VIEW

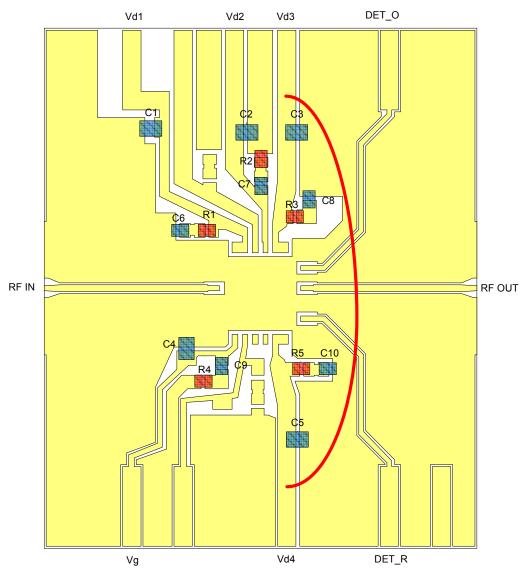
The units are in [mm].



Application Circuit:



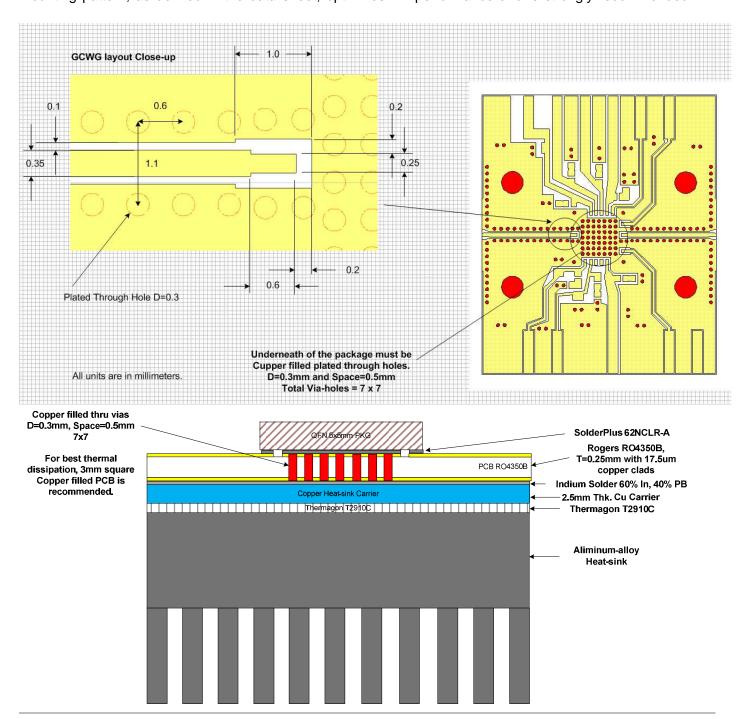
Recommended Application Board Design:
Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. Board is soldered on a gold plated solid cupper block and adequate heat-sinking is required for 16.8W total power dissipation.



Part	Description
C1, C2, C3, C4, C5	1uF capacitor (0603)
C6, C7, C8, C9, C10	0.01uF Capacitor (0402)
R1, R2, R3, R4, R5	10Ω Resistor (0402)

Recommended Application Board Design:

Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. The board material and mounting pattern, as defined in the data sheet, optimizes RF performance and is strongly recommended.





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